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ALD/CVD High-k Metal

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A Critical Materials Report

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RESEARCH METHODOLOGY

TECHCET employs subject matter experts having first-hand experience within the industries, which they analyze. Most of TECHCET's analysts have over 25 years of direct and relevant experience in their field. Our analysts survey the commercial and technical staff of IC manufacturers and their suppliers, and conduct extensive research of literature and commerce statistics to ascertain the current and future market environment and global supply risks. Combining this data with TECHCET's proprietary, quantitative wafer forecast results in a viable long-term market forecast for a variety of process materials.

Readers Note: This report represents the interpretation and analysis of information generally available to the public or released by responsible agencies or individuals. Data was obtained from sources considered reliable. However, accuracy or completeness is not guaranteed.

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Table of Contents

1 Executive Summary 10

2 Scope 13

3 Definitions - Fundamentals of Dielectric Thin Film Deposition 16
3.1 Chemical Vapor Deposition - CVD 16
3.2 Atomic Layer Deposition - ALD 19

4 IC Technology Trends & Roadmaps 22
4.1 Memory Evolution 22
4.1.1 DRAM 23
4.1.2 State of the art 10nm class DRAM 24
4.1.3 Hybrid Memory Cube 27
4.1.4 2D- to 3D-NAND transition 30
4.2 Lithography - Multi-patterning and Hardmasks 35
4.3 Copper Interconnect 40
4.4 Logic Transistor Evolution 41
4.5 Extending FinFET to Horizonal Nanowires GAA FETs 51
4.6 Realizing vertical Logic Going vertical (2.5/3D) 56

5 High-k/Metal Gate Logic & Memory Precursors 59
5.1 Application Description and Current Gate Materials 61
5.2 FEOL Logic Metal Precursor Overview 67
5.3 Future High-k/Metal Gate and Requirements 68
5.4 High-k capacitor precursor for Volatile & Non-Volatile Memory technologies 68
5.5 High-k Current Capacitor materials and precursors 73
5.6 High K Capacitor Market and Forecast 74
5.7 Long Term Metal Precursor Opportunities 3D-NAND 75
5.8 High-k / Metal Gate & Capacitor Market and Forecast 75

6 Interconnect 79
6.1 Interconnect Trends 80
6.2 Metal Plugs and Interconnect Materials CVD/ALD Metals Forecast 82
6.3 Alternative Barrier, Interconnect and Capping Materials 83
6.3.1 Atomic Layer Deposition Development for Barrier Films 84
6.3.2 Copper Cap after CMP 84
6.4 Interconnects at 7 nm and beyond 85
6.4.1 Cobalt Contacts and Interconnects 86
6.4.2 Ruthenium interconnects 88

7 Precursor Delivery and Monitoring 90

8 Market Segmentation & Share 93

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9 Precursor market size and CAGR 97

10 Future Outlook for High-k & Metal Precursors 100
10.1 ALD IP filing and global distribution of IP 100
10.2 High-k IP trends 101

11 Raw material supply chains 103
11.1 Zirconium and Hafnium 104
11.2 Niobium and Tantalum 110
11.3 Rare earth 113
11.4 Tungsten 120
11.5 Cobalt 122
11.5.1 Cobalt in lithium ion batteries 126
11.5.2 Sustainable Procurement Framework for Cobalt 128

12 Competing Industries for ALD-precursors and Global Metal Sourcing 129
12.1 Photovoltaic 130
12.2 MEMS 135
12.3 Display 137
12.4 Emerging ALD markets 139

13 Chemical Supplier Profiles 141
13.1 Supply Value Chain 141
13.2 Adeka 143
13.3 Air Liquide S.A. 144
13.4 Azmax part of Azuma group 146
13.5 BASF 147
13.6 DNF "Dream New Future" 149
13.7 Dow Corning 150
13.8 Digital Speciality Chemicals (DSC) 151
13.9 Dow 152
13.10 Entegris (previously ATMI) 154
13.11 Epivalence 155
13.12 Fujifilm 156
13.13 Gelest, Inc. 157
13.14 H.C. Starck 158
13.15 Kojundo Chemical Laboratory 159
13.16 Merck's EMD Performance Materials (previously Epichem, SAFC Hitech and AZ) 160
13.17 Nanmat Technology Co. Ltd. 162
13.18 Norquay Technology 163
13.19 Nova-Kem LLC 164
13.20 Nanogen Solutions 166
13.21 Pegasus 166
13.22 Praxair 167
13.23 Soulbrain Co., Ltd. 168
13.24 STREM 170

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13.25 TCI Chemicals 171
13.26 Tri Chemical Laboratories 172
13.27 Umicore 173
13.28 UP Chemical Co., Ltd. 174
13.29 Versum Materials, Inc. (previously Air Products Chemical Inc.) 175

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List of Figures

page #

Figure 1: Annual 300mm Equivalent Wafer Starts Logic and Memory (Lita Shon Roy, TECHCET, CMC2017 Dallas) 15
Figure 2: The fundamental differences between continuous, pulsed and atomic layer processing (Source: Fred Roozeboom, TU Eindhoven, High-k Workshop Dresden March 2016).... 18
Figure 3: Overview of ALD tools and technologies used in high volume manufacturing (TECHCET, CMC Conference 2017) 21
Figure 4: DRAM vs. NAND Flash (Samsung 2016).... 23
Figure 5: The DRAM node transitions 65 to 10 nm (TECHCET, March 2017).... 24
Figure 6: Samsungs ultra-thin dielectric layer deposition explained (Samsung 2016)... 25
Figure 7: Schematic cross sections of (above) SK-Hynix HBM module (TechInsights 2015), and (below) Micron HMC (Micron 2012), both showing stacked DRAM chips interconnected by TSV. 27
Figure 8: TSV Stacked Memory Patent Landscape Analysis (Sept. 2016) from KnowMade, a technology intelligence and IP strategy consulting company.... 28
Figure 9: The implications of the transition to 3D-NAND, less dielectrics for multiple patterning but more for the multilayer stack as well as etch hardmasks (Source: Applied Materials).... 31
Figure 10: NAND 300mm wafer forecast showing the 2D- to 3D-NAND transition at full speed today (TECHCET March, 2017).... 32
Figure 11: Intel and Micron use unique silver-doped calchogenide compounds in a cross point architecture for a NVM memory technology. (Source: Intel & Micron).... 33
Figure 12: Ferroelectric hafnium oxide by ALD can be integrated in 3D capacitors (FRAM) in BEOL as well as in a FEOL HKMG stack (FeFETs) (Source: Globalfoundries & Fraunhofer, IEDM 2014).... 34
Figure 13: self-aligned quadruple patterning (SAQP), from left to right: patterning of the first core (brown) onto a mandrel (green); deposition of silicon dioxide (SiO_2) (light blue) by atomic layer deposition (ALD); etching of the first spacers; etching of the mandrel to produce the second core; further deposition of SiO_2 by ALD; and etching of the second spacers and silicon nitride pad (dark blue). The scale bars represent 30 nm. (Coventor, 14 May 2016, SPIE Newsroom) 36
Figure 14: To transfer a pattern on wafer, KrF resist in wide patterns works well, while ArF resist in narrow patterns results in pattern-collapse, requiring the use of a hardmask for selectivity to underlying material during etching. Depending upon the etch scheme, the lower Carbon HardMask (CHM, or Amorphous Carbon Layer, or Spin-On Carbon) may also function as the mask. (Source: DNS Company presentation 2017).. 38
Figure 15: Dimensional scaling under pressure (An Steegen, Imec, ISS 2017).... 39

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Figure 16: Recent trend from top-down lithography to self-alignment and bottom-up patterning approaches (Source: Rob Clarke, TEL, CMC Conference 2017) 42
Figure 17: The evolution of High-k / Metal Gate Transistors, from the first planar 45nm to the latest 14nm node. (Source: Ivo Raajmakers, ASMI 2016)................................ 43
Figure 18: Comparison of CMOS Transistor used today. (A) Planar, (B) FD-SOI and (C) FinFET 44
With respect to dielectrics, the uses in state-of-the-art 10nm FinFET technology are Low-k, High-k, liners, and even dielectric air-gaps (Figure 19).................................. 44
Figure 20: Possible uses for dielectrics in state of the art 10 nm FinFET technology : Low-k, High-k, liners, and even dielectric air-gaps (Source: IBM and Globalfoundries, IEDM 2016).. 45
Figure 21: Gartner roadmap modified by realities 2016 (Source: *Solid State Technology* Seminar Dec 15, 2016) 46
Figure 22: After the introduction at 22nm by Intel of "TriGate" FinFETs, a taller and narrower fin leads to more vertical profile in 14nm, which continues at 10 nm with the vertical profile even more distinct. (Source: Intel technology Forum, March 2017)...... 47
Figure 23: Self-aligned contacts solve misalignment (Source: Kaizad Mistry, Intel 2014). 48
Figure 24: Leading-edge logic node transitions (TECHCET, March 2017) 49
Figure 25: Schematic of partial air spacers (left), and TEM cross-section of finFET gates, showing spacers between gates and contacts (Source: IBM & Globalfoundries, IEDM2016).. 50
Figure 26: A Gate-All-Around (GAA) FET that could come into play at 5nm or 3nm. (Source: École Polytechnique Fédérale De Lausanne) 51
Figure 27: Imec CMOS Roadmap as presented by Ann Steegen at ISS 2017 January 10. 52
Figure 28: IMEC has achieved the CMOS integration of vertically stacked gate-all-around (GAA) silicon nanowire MOSFETs. (IMEC, IEDM2016)... 53
Figure 29: Three principal cross-section simulation of (a) finFET, (b) nanowire, and (c) nanosheet, (Source: IBM) 54
Figure 30: TEM cross section of 5nm-node GAA-FETs by IBM, Samsung and Globalfoundries. (Source IBM). 55
Figure 31: Leti roadmap for introducing monolithic 3D logic scaling at 5nm node. (Source: CEA/Leti 2016).. 57
Figure 32: Schematic diagrams of Intel 22nm node HKMG Tri-Gate P-type MOSFET (PFET) and N-type MOSFET (NFET) showing major performance elements and insets of schematic cross-sections showing gate stack detail for each device. (Source: Tokyo Electron, Materials 7 (2014) 2913) 60
Figure 33: The 65 nm (Intel) CMOS Poly/SiON Gate Dielectric Structure used for 90nm through to 28nm nodes, showing a high resolution TEM cross section of the ~1.2 nm SiON gate dielectric. 62
Figure 34: Device with high-k first gate dielectric structure, which is a simple evolution from Poly/SiON... 63
Figure 35: Cross sections of 14nm node Intel FinFET technology showing pMOS (left) and nMOS (right)... 64

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Figure 36: Planar Devices, Gate-First vs. Gate-Last Replacement Gate technology 66
Figure 37: DRAM vertical stacked capacitors at sub-65nm-node (Source: Hwang 2014). 71
Figure 38: Options for Ferroelectric HfO_2, either as a FEOL or BEOL embedded NVM (Source: Globalfoundries et al, IEDM 2013) 72
Figure 39: Overview of dopants investigated for phase stabilization of ferroelectric HfO2 (Source: NaMLab, Fraunhofer CNT 2014). 73
Figure 40: High-k Precursors for Capacitor (DRAM Memory) 75
Figure 41: High-k & Capacitor Metal Precursor Forecast (Logic, DRAM, NAND & Emerging Memory) 78
Figure 42: ALD barrier application replacing PVD barriers for the lower metallization levels. 80
Figure 43: Revenue Forecast for ALD/CVD Metal Gate, Electrodes, Plug Metal (Metal-0), Barrier Precursors & Seeds. 82
Figure 44: ALD Ru as a barrierless metallization solution for future sub-10 nm interconnects. Void-free filling in sub-10 nm wide single damascene lines using an ALD process in combination with 2.5 Å of ALD TiN interface and post-deposition annealing. (Source: Imec/KU Leuven 2016, *ACS Appl. Mater. Interfaces*, 2016, 8 (39), pp 26119–26125) 88
Figure 45: ZyALD™ and TEMAZ have similar vapor pressures (left), while Thermal Gravimetric Analysis (TGA, right) shows ZyALD has better thermal stability (Source: AirLiquide). 91
Figure 46: Metal and high-k precursor segmentation and market sizes, with the top selling metal precursor as representative for the whole market segment (TECHCET 2017). 94
Figure 47: World-wide market share estimate for leading chemical suppliers 2016/2017. (TECHCET 2017) 95
Figure 48: Global segmentation of the market share estimated for leading chemical suppliers 2016/2017. (TECHCET 2017) 96
Figure 49: The total ALD/CVD High-k & Metal Precursor Market development 2013 to 2020 with an average CAGR of 11%. 97
Figure 50: Filed IP in the field of Atomic Layer deposition (Source: IAMIP AB March 2017). 100
Figure 51: Global filed IP in ALD (Source: IAMIP AB March 2017) 101
Figure 52: High-k IP applications segmented by metal oxide type (Source: Patbase, April 2017) 102
Figure 53: The zirconium chemicals market consumes about 21% of annual zircon production and is the fastest growing segment of zircon consumption.(Alkane 2016) 106
Figure 54: Hafnium demand estimates 2015, no new information is available due to strategic importance (Alkane 2016) 107
Figure 55: The recent price surge in hafnium metal (Lipmann, 2015) 109
Figure 56: The rare earth elements are seventeen chemical elements in the periodic table, specifically the fifteen lanthanides, as well as scandium and yttrium 114
Figure 57 : The history of rare earth element production, in metric tons of rare earth oxide equivalent, between 1950 and 2016. (USGS 2017) 115

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Figure 58: Tungsten mine production and reserves (USGS 2017) 121
Figure 59: Cobalt Demand by industry (Palisade 2016).. 124
Figure 60: World Mine Production and Reserves from USGS 2017: Reserves for Australia, Canada, New Caledonia, the Philippines, South Africa, the United States, and "Other countries" were revised based on company or Government reports. 125
Figure 61: A break down of lithium batteries by types (Research in China 2015) 128
Figure 62: Estimated annual market size of ALD equipment (TECHCET, CMC Conference 2017).. 130
Figure 63: High efficiency cell technologies like the PERC is gaining a bigger market share (IHS Markit Trends in PV Crystalline Technology 2017)................................. 131
Figure 64: A standard Al-BSF cell vs. a PERC Cell (Source: TaiyangNews / PERC Solar Cell Technology 2016).. 132
Figure 65: Required thickness of Al2O3 for different deposition technologies (Source: TaiyangNews / PERC Solar Cell Technology 2016).. 133
Figure 66: As of 2017 Al_2O_3 has taken a 99% market share for back side passivation for PERC technology (7th ITRPV Edition). 134
Figure 67: A segmentation of ALD applications (Source: Nanobakers Oy, 2016) 140

List of Tables

page #

Table 1: OEM Front end process technologies for FinFET and nanowire/nano sheet HVM. 56
Table 2: Critical thermal budget steps summary in a planar FDSOI integration and CoolCube process for top FET in 3D-VLSI. (Source: CEA/Leti and Qualcomm Technologies, VLSI Symposium 2015) 58
Table 3: Dielectric Constant of Transistor Gate and Memory Capacitor Dielectric Material 65
Table 4: Metal ALD / CVD precursor used in production for high-k / metal gate stacks 67
Table 6: Bulk properties of metals commonly used in IC manufacturing (Source: Ed Korczynski, *Solid State Technology* 2016).. 87
Table 7: World primary hafnium production data were not available. Zirconium reserves for Australia were revised based on data from Geoscience Australia. Reserves for Mozambique were based on company reports. Although hafnium occurs with zirconium in the minerals zircon and baddeleyite, quantitative estimates of hafnium reserves were not available. (USGS 2017)... 108
Table 8: Rare earth world mine production and reserves (USGS 2017). 116
Table 9: A table listing the seventeen rare earth elements, their atomic number and symbol, and their main usages (Wikipedia April 2017) 117
Table 10: Organometallic Precursors: Synthesizers and Suppliers to the IC Market .. 142

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